

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-channel Silicon Juncton FET

TF202THC — Electret Condenser Microphone Applications

Features

- · Ultrasmall package facilitates miniaturization in end products.
- · Especially suited for use in electret condenser microphone for audio equipments and telephones.
- · Excellent voltage characteristics.
- · Excellent transient characteristics.
- · Adoption of FBET process.
- · Halogen free compliance.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Gate-to-Drain Voltage	V _{GDO}		-20	V
Gate Current	IG		10	mA
Drain Current	ID		1	mA
Allowable Power Dissipation	PD		100	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol Conditions	Canditions	Ratings			Unit
		min	typ	max	Offic	
Gate-to-Drain Breakdown Voltage	V(BR)GDO	I _G =-100μA	-20			V
Cutoff Voltage	VGS(off)	V _{DS} =5V, I _D =1μA	-0.2	-0.6	-1.0	V

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TF202THC

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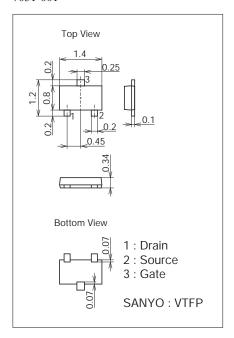
Parameter	Cumbal	Conditions	Ratings			Unit
	Symbol	Conditions	min	typ	max	Unit
Drain Current	IDSS	V _{DS} =5V, V _{GS} =0V	140*		350*	μΑ
Forward Transfer Admittance	yfs	V _{DS} =5V, V _{GS} =0V, f=1kHz	0.5	1.0		mS
Input Capacitance	Ciss	V _{DS} =5V, V _{GS} =0V, f=1MHz		3.5		pF
Reverse Transfer Capacitance	Crss	V _{DS} =5V, V _{GS} =0V, f=1MHz		0.65		pF
[Ta=25°C, V _{CC} =4.5V, R _L =1kΩ, Cin=15pF, See specified Test Circuit.]						
Voltage Gain	GV	V _{IN} =10mV, f=1kHz		-3.0		dB
Reduced Voltage Characteristic	ΔGVV	$V_{IN}=10$ mV, f=1kHz, $V_{CC}=4.5$ V $\rightarrow 1.5$ V		-1.2	-3.5	dB
Frequency Characteristic	ΔGvf	f=1kHz to 110Hz			-1.0	dB
Input Impedance	Z _{IN}	f=1kHz	25			MΩ
Output Impedance	ZO	f=1kHz		1000		Ω
Total Harmonic Distortion	THD	V _{IN} =30mV, f=1kHz		1.2		%
Output Noise Voltage	V _{NO}	V _{IN} =0V, A Curve			-110	dB

 $^{^{\}star}$: The TF202THC is classified by IDSS as follows : (unit : $\mu\text{A}\text{)}$

Marking	E4	E5
Rank	4	5
IDSS	140 to 240	210 to 350

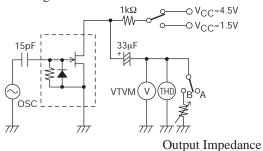
Package Dimensions

unit : mm (typ) 7031-001

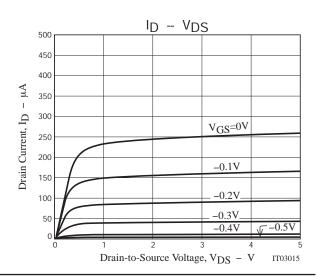


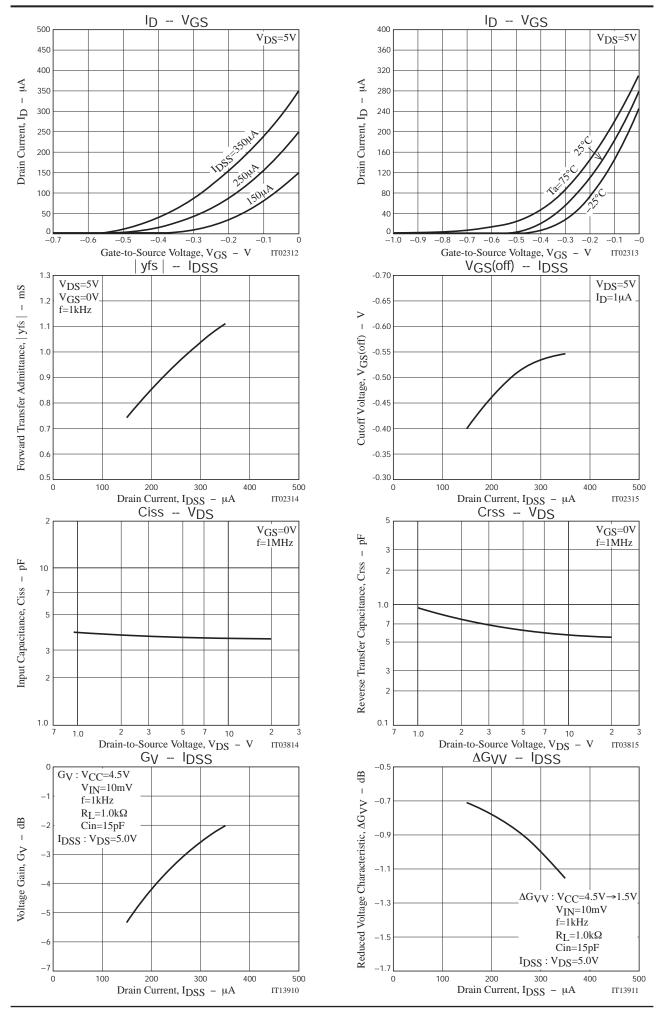
Test Circuit

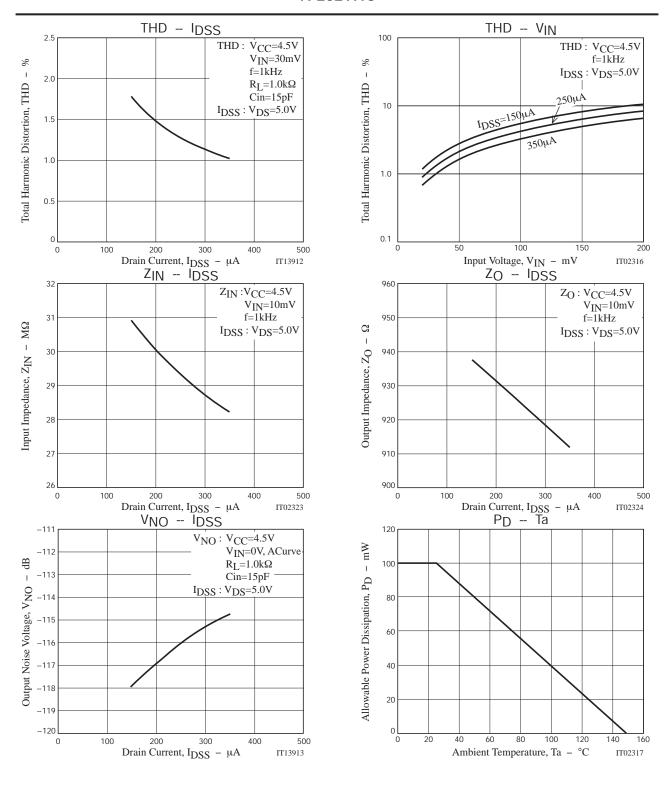
Voltage gain Frequency Characteristic Distortion Reduced Voltage Characteristic



ID - VDS 500 450 400 Drain Current, Ip - µA 350 300 $V_{GS}=0V$ 250 200 -0.1V 150 -0.2V 100 50 Drain-to-Source Voltage, $V_{DS} - V$ IT02310







TF202THC

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